Amendments to the Claims

1. (*Original*) A method of manufacturing a semiconductor device comprising the step of depositing an epitaxial layer based on Group IV elements on a silicon substrate by Chemical Vapor Deposition, and including employing nitrogen or a noble gas as a carrier gas.

2. (*Currently Amended*) A method as claimed in claim 1, ~~which is employed to form~~ the method forming an epitaxial layer based on at least one of the following: silicon, germanium, and carbon. ~~silicon, germanium and/or carbon.~~

3. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises $Si_{1-y}C_y$.

4. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises a SiGe epitaxial layer.

5. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises $Si_{1-x-y}Ge_xC_y$.

6. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises a silicon epitaxial layer.

7. (*Currently Amended*) A method ~~as claimed in any one of the preceding claims,~~ as claimed in claim 2, which is carried out at a low temperature.

8. (*Original*) A method as claimed in claim 7, which is carried out at a temperature of less than about 600°C.

Claims 9-16 (*Cancelled*).

17. (*New*) A method as claimed in claim 3, which is carried out at a low temperature.

18. (*New*) A method as claimed in claim 4, which is carried out at a low temperature.

19. (*New*) A method as claimed in claim 5, which is carried out at a low temperature.

20. (*New*) A method as claimed in claim 6, which is carried out at a low temperature.